

RBV2510S

PRV : 1000 Volts
Io : 25 Amperes

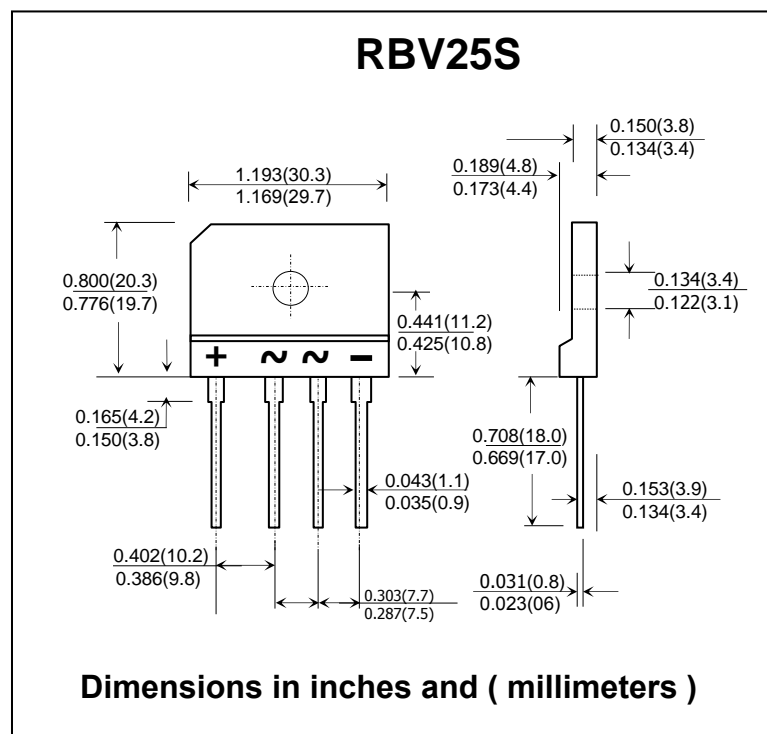
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Rated isolation-voltage 2000 V_{AC}
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-0 rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV2510S	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	1000	V
Maximum RMS Voltage	V _{RMS}	700	V
Maximum DC Blocking Voltage	V _{DC}	1000	V
Maximum Average Forward Current T _c = 55°C	I _{F(AV)}	25	A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}	260	A
Current Squared Time at 1ms ≤ t < 8.3ms.	i ² t	280	A ² S
Maximum Forward Voltage per Diode at I _F = 12.5 A	V _F	1.1	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	10	μA
Typical Thermal Resistance (Note 1)	R _{θJC}	1.0	°C/W
Operating Junction Temperature Range	T _J	- 55 to + 150	°C
Storage Temperature Range	T _{STG}	- 55 to + 150	°C

RATING AND CHARACTERISTIC CURVES (RBV2510S)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

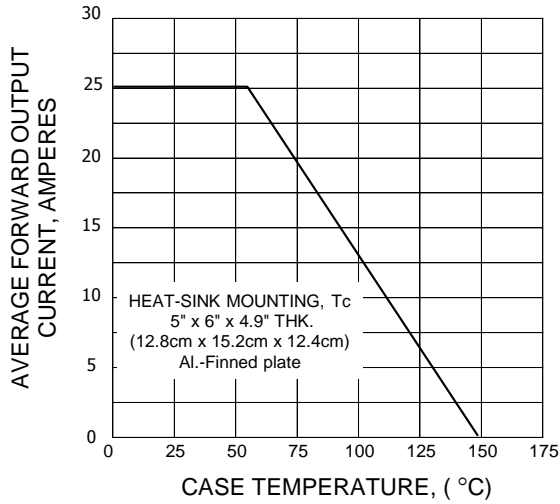


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

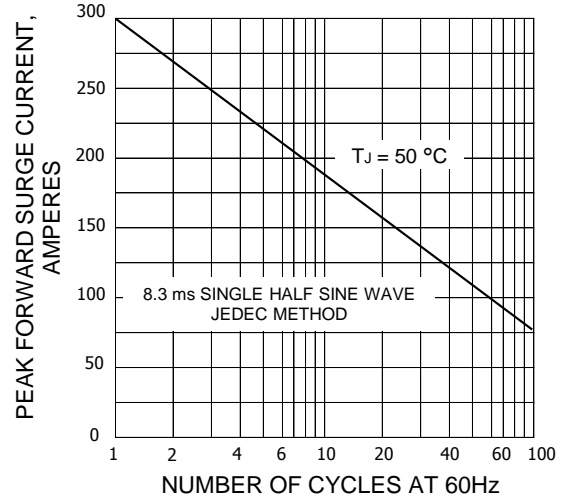


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

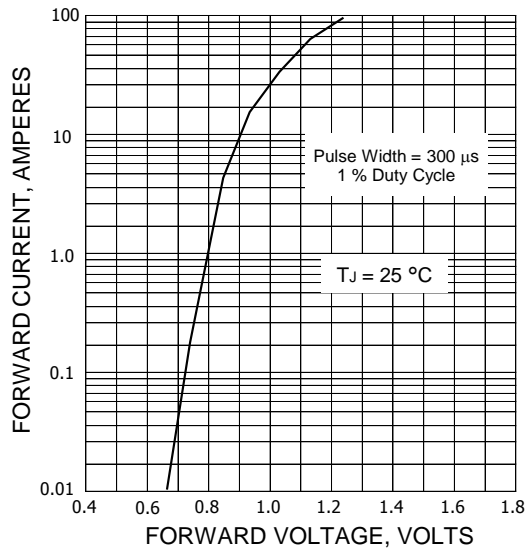


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

